



场效应管

Field Effect Transistor



三极管

Transistor



可控硅

Thyristor



二极管

Diode



集成电路

Chip IC



集成电路模块

Chip IC Module



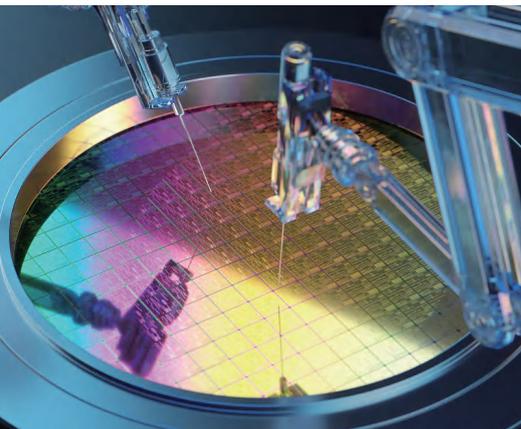






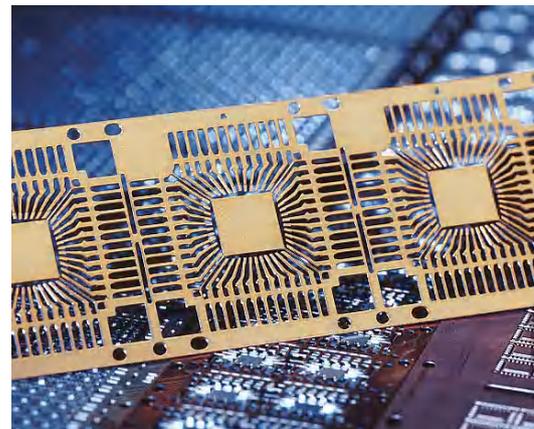
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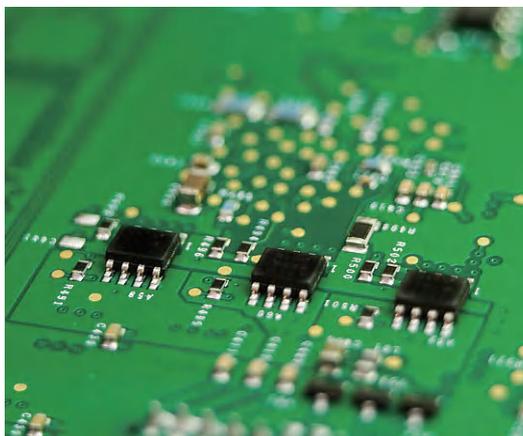
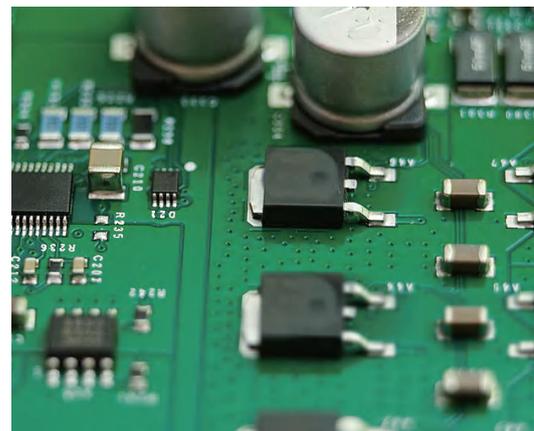
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高质量的电子设备离不开高质量的元器件，高质量的元器件离不开高质量的原材料。当市场对新功能有需求，我们总会尽全力搜寻最合适的物料，以提供最优质的产品与服务。在SMD（表面贴片器件）领域，这一宗旨伴随着科信品牌，见证了无数新型器件的诞生。

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Innovation is the driving force behind the development of KEXIN, which has been engaged in the production,R&D and sales of SMD surface mounted devices for 36 years, always focusing on the miniaturization of SMD surface mounted devices.

New quality electronic equipment begins with new quality components, and new quality components begin with new quality materials.When new features are in demand, we always go back to the very basics of searching for the most appropriate materials in order to provide the products and services of best quality. By sticking to this concept, KEXIN produced numerous new devices in the field of SMD(Surface Mount Devices).

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▶ 场效应管 (FET) 是一种通过电场效应控制电流的电子元件。它依靠电场来控制导电沟道形状, 因此能控制半导体材料中某种类型的沟道的导电性。场效应晶体管有时被称为“单极性晶体管”, 以它的单载流子型作用对比双极性晶体管。场效应管目前有结型场效应管和金属氧化物半导体场效应管。

A Field-Effect Tube (FET) is an electronic component that controls current through an electric field effect. It relies on an electric field to control the shape of the conductive channel, and therefore the conductivity of a certain type of channel in a semiconductor material. Field-effect transistors are sometimes referred to as "unipolar transistors" because of their single-carrier-type action in contrast to bipolar transistors. Currently, there are junction Fets and metal-oxide-semiconductor Fets.

▶ 场效应管应用

- 1.可应用于放大。由于场效应管放大器的输入阻抗很高, 因此耦合电容可以容量较小, 不必使用电解电容器。
- 2.很高的输入阻抗非常适合作阻抗变换。常用于多级放大器的输入级作阻抗变换。
- 3.可以用作可变电阻。
- 4.可以方便地用作恒流源。
- 5.可以用作电子开关。

6.在电路设计上的灵活性大。栅偏压可正可负可零, 三极管只能在正向偏置下工作, 电子管只能在负偏压下工作。另外输入阻抗高, 可以减轻信号源负载, 易于跟前级匹配。

FET Application

1. Can be applied to magnification. Because the input impedance of the FET amplifier is high, the coupling capacitance can be small and the electrolytic capacitor is not necessary.
2. The high input impedance is very suitable for impedance transformation. It is often used for impedance conversion in the input stage of multistage amplifiers.
3. Can be used as a variable resistor.
4. It can be easily used as a constant current source.
5. Can be used as an electronic switch.
6. Great flexibility in circuit design. The grid bias can be positive or negative or zero, triode can only work under positive bias, and the tube can only work under negative bias. In addition, the input impedance is high, which can reduce the load of the signal source and make it easy to match the previous level.

应用场景

APPLICATION



N沟道场效应管：N 沟道 MOSFET 通过电子形成电流沟道。因此在 MOSFET 被激活和导通时，电子即可通过电流轻松快速地移动。出于 N 沟道 MOSFET 的特殊性，在相同的 RDS(on) 值下，其载流子的迁移率约为 P 沟道器件的 2 到 3 倍，而 P 沟道芯片尺寸则必须为 N 沟道芯片的 2 到 3 倍。因此，大电流应用通常首选 MOSFET 晶体管 N 沟道器件。

An N-Channel MOSFET uses electrons to create a current channel. This allows electrons to move quickly and easily through the current when the MOSFET is activated and switched on. Because of the specific characteristics of N-channel MOSFET, the mobility of the carriers is approximately two to three times higher than that of a P-channel for the same RDS(on) value, and the P-channel chip must be two to three times the size of the N-channel. For this reason, using MOSFET transistor N-channels for high current applications is often the preferred choice.

N-CHANNEL MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{GS(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KK5001DS	N-Channel	20	5	±10	0.4 ~ 1	1.25	20	16.8	SOT-23-3
2KK5002	N-Channel	20	2.8	±8	0.62 ~ 1.2	1.25	45	4	SOT-23
2KK5003	N-Channel	20	2.8	±8	0.6 ~ 1	1.25	45	4	SOT-23-3
2KK5004EDS	N-Channel	20	6	±8	0.4 ~ 1.1	1.25	17	14	SOT-23-3
2KK5008DS	N-Channel	20	4.9	±8	0.45 ~ 0.85	1.25	27	11.2	SOT-23-3
2KK5010E	N-Channel	20	6.5	±8	0.4 ~ 1.1	1.4	16	10	SOT-23-3
2KK5014DFN	N-Channel	20	8	±10	0.4 ~ 1	1.4	25	10	DFN2×2-6
2KK5016	N-Channel	20	0.238	±10	0.5 ~ 1.5	0.3	1500	10	SOT-523
2KK5018DFN	N-Channel	20	8	±8	0.4~1.1	1.25	15	14	DFN2×2-6
2KK5039DFN	N-Channel	20	60	±12	0.5 ~ 1.1	42	5.5	32	PDFN3.3×3.3-8
2KK5051DFN	N-Channel	20	12	±12	0.4 ~ 1	1.4	7.6	10	DFN2×2-6
2KK5776	N-Channel	20	0.75	±12	0.35 ~ 1.1	0.15	380	4	SOT-723
2KK6000DFN	N-Channel	20	8	±8	0.4 ~ 1.1	2.8	16	10	DFN2×2-6
2KK6009DFN	N-Channel	20	0.75	±10	0.35 ~ 1.1	0.1	380	1.8	DFN1006-3
2KK7005	N-Channel	20	25	±12	0.5 ~ 1.2	2.5	4	64.9	SOP-8
2KK5047DFN	N-Channel	25	100	±12	1.2 ~ 1.9	64	3.2	9	PDFN5×6-8
2KK5005	N-Channel	30	5.8	±12	0.7 ~ 1.4	1.4	27.3	9.7	SOT-23
2KK5006DS	N-Channel	30	5.8	±12	0.7 ~ 1.4	1.4	27.3	9.7	SOT-23-3
2KK5007DS	N-Channel	30	4	±12	0.6 ~ 1.4	1.4	55	4.34	SOT-23-3
2KK5022	N-Channel	30	5.8	±20	0.7 ~ 1.4	1.4	27.3	9.7	SOT-23-6
2KK5048DFN	N-Channel	30	150	±20	1.3 ~ 2.3	64	1.2	46	PDFN5×6-8
2KK5075DFN	N-Channel	30	36	±20	1.1 ~ 1.9	50	7	20.5	PDFN5×6-8
2KK5086DFN	N-Channel	30	50	±20	1 ~ 2	42	5	54	PDFN3.3×3.3-8
2KK5089DFN	N-Channel	30	10	±8	0.45 ~ 1	2	16	20	DFN2×2-6
2kk5094DFN	N-Channel	30	11	±20	1.1 ~ 2.2	3.5	12	13	DFN2×2-6
2KK5117	N-Channel	30	20	±20	1 ~ 2	1.5	9	21	SOP-8
2KK5128	N-Channel	30	120	±20	1.2 ~ 2.4	100	5.6	59	TO-252
2KK5773DFN	N-Channel	30	45	±20	1.1 ~ 1.9	25	6	44	PDFN3.3×3.3-8
2KK5774DFN	N-Channel	30	45	±20	1.1 ~ 1.9	25	6	44	PDFN3.3×3.3-8
2KK5777DFN	N-Channel	30	100	±20	1.1 ~ 1.9	50	4.7	63	PDFN5×6-8
2KK5779DFN	N-Channel	30	50	±20	1 ~ 2.2	25	14	45	PDFN3.3×3.3-8
2KK6003DFN	N-Channel	30	40	±20	1 ~ 3	31.2	11	61.5	PDFN3.3×3.3-8
2KK6006DFN	N-Channel	30	9	±12	1 ~ 2.5	50	19	5	PDFN3.3×3.3-8
2KK6008DFN	N-Channel	30	45	±20	0.7 ~ 1.6	25	6.5	25.2	PDFN3.3×3.3-8
2KK7002	N-Channel	30	7	±20	1 ~ 3	2.5	40	24	SOP-8
2KK7003	N-Channel	30	10	±20	1.4 ~ 2.5	3.1	26	9.8	SOP-8
2KK7110	N-Channel	30	18	±20	1.3 ~ 2.5	3.4	7.5	37	SOP-8
2KK5046DFN	N-Channel	40	200	±20	1 ~ 3	92.6	1.2	115	PDFN5×6-8
2KK5049DFN	N-Channel	40	50	±20	1 ~ 2.5	50	6.5	82	PDFN5×6-8
2KK5050DFN	N-Channel	40	110	±20	1.2 ~ 2.2	75	3.9	60	PDFN5×6-8
2KK5056	N-Channel	40	60	±20	1 ~ 2.5	40	10.5	82	TO-252
2KK5074DFN	N-Channel	40	150	±20	1 ~ 2.4	78	3.5	50	PDFN5×6-8
2KK5082DFN	N-Channel	40	35	±20	1 ~ 2.2	25	19	17	PDFN3.3×3.3-8
2KK5092	N-Channel	40	70	±20	1 ~ 2.2	150	3.8	49	TO-252
2KK5096DFN	N-Channel	40	100	±20	1~2	69	5.3	12	PDFN5×6-8
2KK5100DFN	N-Channel	40	40	±20	1.1 ~ 2.1	36.7	14.5	27.8	PDFN3.3×3.3-8
2KK5120DFN	N-Channel	40	150	±20	1 ~ 2	92.6	2.4	75	PDFN5×6-8
2KK7004	N-Channel	40	11	±20	1 ~ 3	2.5	16	9	SOP-8
2KK7108	N-Channel	40	17	±20	1 ~ 2	3.1	12.5	27.2	SOP-8
2KK6013DFN	N-Channel	50	0.3	±20	0.8 ~ 1.5	0.25	2000	1.6	DFN1006-3

N-CHANNEL MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{GS(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KK5009	N-Channel	60	0.3	±20	1 ~ 2.5	0.35	2500	0.8	SOT-23
2KK5013	N-Channel	60	3.7	±20	1 ~ 2	1.4	88.9	9	SOT-23-3
2KK5030	N-Channel	60	4	±20	1 ~ 2	3	120	13	SOT-223
2KK5115DFN	N-Channel	60	80	±20	1.1 ~ 2.1	52	9.5	45	PDFN5×6-8
2KK5125DFN	N-Channel	60	80	±20	1.5 ~ 2.5	120	11	83	PDFN5×6-8
2KK5778DFN	N-Channel	60	41	±20	1.2 ~ 2.5	28	12.2	16.6	PDFN3.3×3.3-8
2KK6014DFN	N-Channel	60	95	±20	1.2 ~ 2.2	120	3.4	93	PDFN5×6-8
2KK7106	N-Channel	60	12	±20	1 ~ 2.5	2	16	58	SOP-8
2KK7107	N-Channel	60	6	±20	1.2 ~ 2.5	3.1	39	8.5	SOP-8
2KK5122DFN	N-Channel	75	65	±20	2 ~ 4	78	8.25	106	PDFN5×6-8
2KK5068	N-Channel	80	60	±20	2 ~ 4	140	8.5	100	TO-252
2KK5076DFN	N-Channel	80	48	±20	1.3 ~ 2.3	56	8.5	36	PDFN5×6-8
2KK5102DFN	N-Channel	80	160	±20	1.2 ~ 2	167	3.3	90	PDFN5×6-8
2KK5012	N-Channel	100	1.6	±16	1 ~ 2.5	1.3	170	2.5	SOT-23-3
2KK5028	N-Channel	100	2.6	±20	1 ~ 3	1.6	135	14	SOT-223
2KK5041DFN	N-Channel	100	60	±20	1 ~ 2.2	105	11.5	58	PDFN5×6-8
2KK5042DFN	N-Channel	100	50	±20	1 ~ 2.2	105	12.6	58	PDFN5×6-8
2KK5045	N-Channel	100	41	±20	2 ~ 4	39	19.5	3.5	TO-252
2KK5055	N-Channel	100	4	±20	1 ~ 2.5	30	220	6.7	TO-252
2KK5059DFN	N-Channel	100	20	±20	1.3 ~ 2.5	2	40	39	PDFN5×6-8
2KK5064	N-Channel	100	42	±20	1.3 ~ 2.5	160	58	110	TO-252
2KK5081DFN	N-Channel	100	100	±20	2.3 ~ 4.3	215	6	80	PDFN5×6-8
2KK5095	N-Channel	100	10.8	±20	1.7 ~ 2.7	35.8	150	6.7	TO-252
2KK5116	N-Channel	100	33	±20	1 ~ 2	54	26	90	TO-252
2KK5124DFN	N-Channel	100	38	±20	1.4 ~ 2.6	28	26	17	PDFN3.3×3.3-8
2KK6007DFN	N-Channel	100	53	±20	1.2 ~ 2.2	119	9.1	63	PDFN5×6-8
2KK7006	N-Channel	100	13.5	±20	1.3 ~ 2.3	3.1	10.6	42	SOP-8
2KK5011	N-Channel	110	5	±20	1 ~ 2.5	1.6	136	14	SOT-23-6
2KK5037	N-Channel	110	3	±20	1 ~ 3	1.25	240	2.5	SOT-23-3
2KK5058	N-Channel	110	3	±20	1 ~ 2.5	1.6	160	14	SOT-23-6
2KK5021	N-Channel	130	2.3	±20	2 ~ 4	1.6	190	4.2	SOT-23-3
2KK5026	N-Channel	150	2.8	±20	2 ~ 4	2.2	305	4.9	SOT-233
2KK5035DFN	N-Channel	150	30	±20	2 ~ 4	96	38	35	PDFN5×6-8
2KK5054	N-Channel	150	15	±20	1.5 ~ 2.5	30	255	15.5	TO-252
2KK5062	N-Channel	150	20	±20	2 ~ 4	50	80	39.1	TO-252
2KK5097DFN	N-Channel	150	17	±20	4 ~ 4	38	95	54	PDFN3.3×3.3-8
2KK7104	N-Channel	150	2.8	±20	2 ~ 4	2.2	220	4.9	SOP-8
2KK7109	N-Channel	150	5.2	±20	2 ~ 4	3.5	53	35.8	SOP-8
2KK5052	N-Channel	200	18	±30	2 ~ 4	140	150	27.5	TO-252
2KK5053	N-Channel	250	18	±30	2 ~ 4	120	160	17.5	TO-252
2KK5067	N-Channel	650	11.5	±30	3 ~ 4	101	360	19	TO-252
2KK5104	N-Channel	650	2	±30	2 ~ 4	44	2200	13	TO-252
2KK5106	N-Channel	650	3	±30	2 ~ 4	44	1400	19	TO-252
2KK5108	N-Channel	650	4	±30	2 ~ 4	44	1200	19	TO-252
2KK5110	N-Channel	650	5	±30	2.5 ~ 4.5	44	1000	19	TO-252
2KK5112	N-Channel	650	8	±30	2 ~ 4	44	600	13	TO-252
2KK5113	N-Channel	650	11	±30	2 ~ 4	44	360	13	TO-252
2KK5103	N-Channel	700	7	±30	2.5 ~ 4	150	600	13	TO-252
2KK5105	N-Channel	700	2	±30	2 ~ 4	44	2200	13	TO-252
2KK5107	N-Channel	700	3	±30	2 ~ 4	44	1400	19	TO-252
2KK5109	N-Channel	700	4	±30	2 ~ 4	44	1200	19	TO-252
2KK5111	N-Channel	700	5	±30	2.5 ~ 4.5	44	1000	19	TO-252
2KK5114	N-Channel	700	11	±30	2 ~ 4	44	360	33	TO-252

P沟道场效应管：P沟道 MOSFET 采用空穴流作为载流子，其迁移率小于 N 沟道 MOSFET 中的电子流。就功能而言，二者的主要区别在于 P 沟道 MOSFET 需要从栅极到源极的负电压 (VGS) 才能导通，而 N 沟道 MOSFET 则需要正 VGS 电压。

A P-Channel MOSFET uses hole flow as the charge carrier, which has less mobility than the electron flow used in N-channel MOSFET. In functional terms, the main difference is that P-channel MOSFET require a negative voltage from the gate to the source (VGS) to turn on (as opposed to an N-channel MOSFET, which requires a positive VGS voltage).

P-CHANNEL MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	Vgs(th) (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KJ6056	P-Channel	-150	-21	±20	-0.7 ~ -2	80	66	66	TO-252
2KJ6029	P-Channel	-100	-18	±20	-1 ~ -3	70	120	70	TO-252
2KJ6031	P-Channel	-100	-3	±20	-1 ~ -3	3.1	230	25	SOT-223
2KJ6021	P-Channel	-60	-3.5	±20	-1 ~ -2.5	1.25	120	14	SOT-23-3
2KJ6033	P-Channel	-60	-3.5	±20	-1 ~ -2.5	1.6	130	14	SOT-23-6
2KJ7006	P-Channel	-60	-6.2	±20	-1 ~ -3	3.1	50	46.5	SOP-8
2KJ6011	P-Channel	-50	-0.13	±20	-0.8 ~ -2	0.225	10000	6	SOT-23
2KJ6024	P-Channel	-40	-40	±20	-1.5 ~ -3	80	14	72	TO-252
2KJ6048DFN	P-Channel	-40	-14	±20	-1.1 ~ -2.2	3.5	42	45	PDFN3.3×3.3-8
2KJ6059DFN	P-Channel	-40	-35	±20	-1 ~ -2.5	26	18.5	42	PDFN5×6-8
2KJ6061	P-Channel	-40	15	±20	-1.1 ~ -2.2	66.5	43	52	TO-252
2KJ6062DFN	P-Channel	-40	-30	±20	-1.1 ~ -2.1	6.25	17	42	PDFN3.3×3.3-8
2KJ7008	P-Channel	-40	-13	±20	-1.3 ~ -2.5	2.5	18	40	SOP-8
2KJ6005	P-Channel	-30	-4.2	±12	-0.4 ~ -1.3	1.4	53	9.4	SOT-23
2KJ6006	P-Channel	-30	-4.2	±12	-0.4 ~ -1.3	1.4	53	9.4	SOT-23-3
2KJ6010	P-Channel	-30	-2.6	±20	-1 ~ -3	1.4	166	9	SOT-23-3
2KJ6012	P-Channel	-30	-4.1	±20	-1 ~ -3	1.4	64	14.3	SOT-23-3
2KJ6015	P-Channel	-30	-4.1	±20	-1 ~ -3	1.4	64	14.3	SOT-23-6
2KJ6028	P-Channel	-30	-50	±20	-1 ~ -2	58	11	11	TO-252
2KJ6032	P-Channel	-30	-6	±12	-0.5 ~ -1.1	1.21	53	14	SOT-23-3
2KJ6043DFN	P-Channel	-30	-36	±25	-1 ~ -2	48	12.3	50	PDFN5×6-8
2KJ6045DFN	P-Channel	-30	-50	±20	-1 ~ -2	35.7	18	45	PDFN3.3×3.3-8
2KJ6047DFN	P-Channel	-30	8	±20	-1.1 ~ -2.3	2.8	53	12	DFN2×2-6
2KJ6049DFN	P-Channel	-30	-29	±20	-1 ~ -2	4.1	27	18	PDFN3.3×3.3-8
2KJ6055DFN	P-Channel	-30	-34	±25	-1 ~ -2.1	30	12.3	50	PDFN3.3×3.3-8
2KJ7001	P-Channel	-30	-5.3	±20	-1 ~ -3	2.5	80	14	SOP-8
2KJ7003	P-Channel	-30	-12	±20	-1 ~ -2	2.5	22	17	SOP-8
2KJ7005	P-Channel	-30	-25	±20	-1 ~ -2.5	3.5	14	65	SOP-8
2KJ7103DFN	P-Channel	-30	-6	±20	-1 ~ -2.5	2.9	50	12	PDFN3.3×3.3-8
2KJ7112DFN	P-Channel	-30	-0.57	±10	-0.45 ~ -1	0.25	650	145	DFN1006-3
2KJ7116DFN	P-Channel	-30	-75	±20	-1 ~ -2	45	13	65	PDFN5×6-8
2KJ7117DY	P-Channel	-30	-20	±20	-1.3 ~ -2.4	2.5	6.8	110	SOP-8
2KJ7118DFN	P-Channel	-30	-36.1	±20	-1 ~ -2.5	25	19	27.6	PDFN3.3×3.3-8
2KJ005PDFN	P-Channel	-20	-4.1	±12	-0.45 ~ -1	1.4	45	10	DFN2×2-6
2KJ6001	P-Channel	-20	-2.3	±12	-0.45 ~ -1	1.25	100	5.8	SOT-23
2KJ6002	P-Channel	-20	-2.4	±12	-0.45 ~ -0.95	0.9	100	4.5	SOT-23-3
2KJ6003	P-Channel	-20	-5	±10	-0.5 ~ -0.9	1.25	40	10	SOT-23
2KJ6004	P-Channel	-20	-5	±10	-0.3 ~ -0.9	1.5	43	10	SOT-23-3
2KJ6007	P-Channel	-20	-6	±8	-0.3 ~ -1	1.25	29.8	10.1	SOT-23-3
2KJ6008EDS	P-Channel	-20	-5	±8	-0.3 ~ -0.9	1.5	45	11	SOT-23-3
2KJ6025	P-Channel	-20	-3.5	±10	-0.45 ~ -0.95	1.25	80	8	SOT-23-3
2KJ6036DFN	P-Channel	-20	-60	±8	-0.45 ~ -0.9	25	4	101	PDFN5×6-8
2KJ6038	P-Channel	-20	-8	±12	-0.4 ~ -1.2	1.2	18	35	SOT-23-3
2KJ6046DFN	P-Channel	-20	-1.4	±6	-0.4 ~ -1.2	0.1	480	2.8	DFN1006-3
2KJ6050DFN	P-Channel	-20	-16	±12	-0.4 ~ -1	18	18	35	DFN2×2-6
2KJ6053DFN	P-Channel	-20	-4	±8	-0.4 ~ -1	0.7	100	7.2	DFN2×2-6
2KJ6054	P-Channel	-20	-6	±12	-0.5 ~ -1	2.8	50	12	SOT-223
2KJ6057DFN	P-Channel	-20	-2.5	±12	-0.45 ~ -0.9	0.27	127	3	DFN1006-3
2KJ6060DFN	P-Channel	-20	-60	±12	-0.45 ~ -1	25	3.5	228	PDFN5×6-8
2KJ7004	P-Channel	-20	-5	±10	-0.4 ~ -0.9	2	85	12	SOP-8
2KJ7105DFN	P-Channel	-20	-40	±8	-0.3 ~ -0.9	29	9.5	44	PDFN3.3×3.3-8
2KJ7107DFN	P-Channel	-20	-6	±8	-0.45 ~ -0.95	1.21	35	6.3	DFN2×2-6

P-CHANNEL MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{Gs(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KJ7110DFN	P-Channel	-20	-0.66	±12	-0.35 ~ -1.1	0.1	500	1.6	DFN1006-3
KI3415P	P-Channel	-20	-5	±8	-0.5 ~ -1	1.5	40	11	SOT-23
2KJ6013DFN	P-Channel	-12	-15	±12	-0.4 ~ -1	18	15	50	DFN2×2-6
KI001P	P-Channel	-12	-2.8	±8	-0.4 ~ -1.1	1.2	100	10	SOT-23
KI007P	P-Channel	-12	-3.5	±12	-0.5 ~ -1.3	1	65	10	SOT-23
KI009P	P-Channel	-12	-4	±12	-0.4 ~ -1	1	52	10	SOT-23
2KJ6093	P-Channel	-250	-3	±20	-2 ~ -4	100	2500		TO-252
2KJ6094	P-Channel	-450	-3	±20	-2 ~ -4	100	6000		TO-252
2KJ6095	P-Channel	-500	-0.3	±20	-2 ~ -4	2.5	150000		SOT-223
2KJ6096	P-Channel	-500	-3	±20	-2 ~ -4	100	7000		TO-252
2KJ6097	P-Channel	-200	-6	±20	-2 ~ -4	100	834		TO-252

双N沟道：MOSFET可最大限度地减少电路板占用空间，最大限度地降低寄生电感并降低功耗。典型应用包括直流-直流转换器、系统电压轨以及负载点。

Dual N-Channel：MOSFET minimize board footprint, minimize parasitic inductance, and reduce power consumption. Typical applications include DC-DC converters, system voltage rails, and load points.

DUAL N MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{Gs(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KK5123DFN	Dual N	18	12	±12	0.4~1	2	7.2	17	DFN3×2-6
2KK5017	Dual N	20	4.3	±12	0.45 ~ 1	1.25	24	6.2	SOT-23-6
2KK5019	Dual N	20	7	±8	0.4 ~ 1.1	1.5	20	4.2	SOT23-6
2KK7102	Dual N	20	6.5	±10	0.5 ~ 1.5	2	25	7	SOP-8
2KK7103	Dual N	20	6	±12	0.6 ~ 2	1.25	15.2	5	SOP-8
2KK5063	Dual N	30	0.1	±20	0.8 ~ 1.5	0.2	4000	1.7	SOT-363
2KK5080DFN	Dual N	30	50	±20	1~2.2	25	14	45	PDFN3.3×3.3-8
2KK5084	Dual N	30	14	±20	1~2	1.5	9	21	SOP-8
2KK5119DFN	Dual N	30	40	±20	1~2.2	25	18	21	PDFN3.3×3.3-8
2KK5121	Dual N	30	3.7	±20	1~2	1.15	73	4.05	SOT-23-6
2KK5782	Dual N	30	12	±20	1.3~2.4	2	18	17	SOP-8
2KK6012DFN	Dual N	30	40	±20	1~3	31.2	13	71	PDFN3.3×3.3-8
2KK7105	Dual N	30	8	±20	1.2~2.4	2	26	15	SOP-8
2KK5126	Dual N	40	15	±20	1~3	2.5	19	9	SOP-8
2kk5783DFN	Dual N	40	35	±20	1~2.2	25	19	17	PDFN3.3×3.3-8
2KK5784DFN	Dual N	40	55	±20	1.1~2.2	49	9	54	PDFN5×6-8
2KK6005DFN	Dual N	60	20	±20	1~2.5	62	44	13	PDFN5×6-8
2KK5780DFN	Dual N	100	31	±20	1~3	35	28	24	PDFN5×6-8

双P沟道：MOSFET非常适合便携式电子应用：负载开关和电源管理、电池充电和保护电路。

Dual P-Channel：MOSFET are ideal for portable electronic applications: load switching and power management, battery charging and protection circuits.

DUAL P MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{Gs(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(mΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2KJ7101	DUAL P	-30	-4.9	±20	-1 ~ -3	2	95	16	SOP-8
2KJ6030	DUAL P	-20	-6	±12	-0.4 ~ -1.4	2	30	18	SOP-8
2KJ6051	DUAL P	-20	-0.6	±8	-0.5 ~ -0.9	0.3	520	1.44	SOT-363
2KJ7102DFN	DUAL P	-20	-30	±12	-0.65 ~ -1.2	29	25	33	PDFN3.3×3.3-8
2KJ7104DFN	DUAL P	-20	-4.5	±8	-0.45 ~ -0.95	1.21	40	6.3	DFN2×2-6
2KJ7114DFN	DUAL P	-20	-6	±8	-0.45 ~ -0.95	1.21	40	6.3	DFN2×2-6

N+P: 互补式功率 MOSFET 以高、低边配置将 N 沟道与 P 沟道 MOSFET 集成至单个封装中。此类 MOSFET 互补对不仅能提高设计效率, 亦可简化产品结构, 进而打造出成本优化型解决方案, 应用包括 DC-DC 转换、电机控制、电池管理以及车载充电器等。

N+P: Complementary power MOSFET integrate N-channel and P-channel MOSFET in a single package in high and low-side configurations. These complementary MOSFET pairs not only improve design efficiency, but also simplify product structure to create cost-optimized solutions for applications including DC-DC conversion, motor control, battery management, and on-board chargers.

N+P MOSFET

(P/N)	POLAR (CH)	VDSS (V)	ID (A)	VGSS (V)	V _{Gs(th)} (V)	PD(W) (TC=25°C)	RDS(on) Max.(MΩ) VGS=4.5V	Qg Typ.(nC) VGS=4.5V	PACKAGE
2NP01	N+P	30	6	±20	1.2 ~ 2.4	2	42	5.2	SOP-8
		-30	-6.5		-1.3 ~ -2.4	2	44	13.6	
2NP02	N+P	20	3.4	±8	0.4 ~ 1	1.1	65	2.9	SOT-23-6
		-20	-2.5		-0.4 ~ -1	1.1	75	8.5	
2NP03	N+P	12	4.5	±8	0.4 ~ 1	6.5	29	9.7	DFN2×2-6
		-12	-4.5		-0.4 ~ -1	6.5	61	13.1	
2NP04	N+P	30	4	±20	0.8 ~ 2	1.48	80	4.6	SOP-8
		-30	-4		-0.8 ~ -2	1.48	80	13	
2NP05	N+P	20	4.5	±8	0.4 ~ 1	1.9	29	9.7	DFN2×2-6
		-20	-4.5		-0.4 ~ -1	1.9	61	13.1	
2NP06	N+P	40	8	±20	1 ~ 2.5	2	23	12	SOP-8
		-40	-7		-1 ~ -2.5	2	30	13	
2NP07	N+P	30	5	±20	1 ~ 3	2	40	16	SOP-8
		-30	-5		-1 ~ -3	2	80	14	
2NP08	N+P	30	18	±20	1 ~ 2.5	14	30	12	TO252-5
		-30	-14		-1 ~ -2.5	14	44	21	
2NP09	N+P	40	32	±20	1 ~ 2.5	25	25	5.5	PDFN5×6-8
		-40	-22		-1 ~ -2.5	25	62	9	
2NP10	N+P	40	40	±20	1 ~ 2.5	42	22	18	PDFN5×6-8
		-40	-40		-1 ~ -2.5	36	35	42	
2NP11	N+P	30	50	±20	1 ~ 2.2	25	14	18	PDFN5×6-8
		-30	-50		-1 ~ -2	25	18	42	
2NP12	N+P	60	0.3	±20	1 ~ 2.5	1.15	3000	0.8	SOT23-6
		-60	-0.18		-0.8 ~ -2	1.15	5000	6	
2NP13	N+P	30	4.3	±20	1 ~ 3	1.15	70	4.2	SOT23-6
		-30	-4.1		-1 ~ -3	1.15	87	14.3	
2NP14	N+P	20	1.06	±12	0.45 ~ 0.9	0.45	500	0.5	SOT-563
		-20	-0.7		-0.45 ~ -0.9	0.45	1000	0.5	
2NP15	N+P	30	25	±20	1.3 ~ 2.4	14	32	11.3	PDFN3.3×3.3-8
		-30	-24		-1.3 ~ -2.4	20	57	19	
2NP16	N+P	40	32	±20	1 ~ 2.5	25	25	5.5	TO-252-5
		-40	-22		1 ~ -2.5	25	62	9	
2NP17	N+P	60	27	±20	1 ~ 2.2	41.7	39	19	PDFN5×6-8
		-60	-18		-1 ~ -2.5	41.7	116	11.2	
2NP18	N+P	60	13	±20	1 ~ 2.2	7.3	39	19	SOP-8
		-60	-7		-1 ~ -2.5	7.3	116	11.2	
2NP19	N+P	100	13	±20	~ 2.5	41.7	120	26.2	PDFN5×6-8
		-100	-18		-1 ~ -2.5	41.7	120	70	
2NP20	N+P	20	2	±10	0.45 ~ 0.9	0.33	91	736.6	SOT-363
		-20	-2		-0.45 ~ -0.9	0.33	285	622.4	
2NP21	N+P	20	2	±10	0.45 ~ 1	1.4	72	2.7	DFN3×2-8
		-20	-1.8		-0.45 ~ -1	1.4	146	3	

结型场效应管：是单极场效应管中最简单的一种，可分为 N 沟槽和 P 沟槽两种。

Junction FET: It is the simplest kind of unipolar FET, which can be divided into N-groove and P-groove two kinds.

JFET

(P/N)	POLAR (CH)	V _{GDS} (V)	I _D (A)	I _G (A)	V _{GSS} (V)	I _{DSS} (mA)	P _D (W) (TC=25°C)	C _{iss} Typ.(pF)	PACKAGE
2SK303	N-Channel	30	0.02	0.01	-30	0.6-12	0.2	5	SOT-23

SOT SERIES PACKAGE



SOT-23



SOT-23-3



SOT-23-6



SOT-223



SOT-363



SOT-523



SOT-723

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DFN SERIES PACKAGE



DFN2x2-6



PDFN3.3x3.3-8



PDFN5x6-8



DFN1006-3

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TO SERIES PACKAGE



TO220



TO252



TO252-5

...

SOP SERIES PACKAGE



SOP-8

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▶ 可控硅(Silicon Controlled Rectifier) 简称SCR，是一种大功率电器元件，也称晶闸管。它具有体积小、效率高、寿命长等优点。是一种具有四个层次（P1N1P2N2）和三个PN结的大功率半导体器件，其核心工作原理在于通过控制极（G极）上的电流来改变其内部的电阻值，从而控制主电路（由阳极A和阴极K组成）的通断状态。在自动控制系统中，可作为大功率驱动器，实现用小功率控制件控制大功率设备。它在交直流电机调速系统、调功系统及随动系统中得到了广泛的应用。

(Silicon Controlled Rectifier)referred to as SCR, is a high-power electrical component, also known as thyristor. It has the advantages of small size, high efficiency and long life. It is A high-power semiconductor device with four levels (P1N1P2N2) and three PN junctions. Its core working principle is to change the internal resistance value by controlling the current on the pole (G pole), so as to control the on-off state of the main circuit (composed of anode A and cathode K). In the automatic control system, it can be used as a high-power driving device to realize the control of high-power equipment with low-power control. It has been widely used in AC and DC motor speed control system, power regulation system and servo system.

▶ 可控硅应用

可控硅的核心优势在于其高度的可控性，通过调整控制极的电流或电压，可以精确控制主回路的导通与截止，从而实现对大电流的精确控制。

此外，可控硅还具备耐压高、正向压降小、无机械噪声和磨损等优点。它被广泛应用于各种电子设备和电子产品中，如家用电器、工业控制、电力电子等领域，作为可控整流、逆变、变频、调压、无触点开关等关键部件。

Thyristor Application

The core advantage of thyristor is its high controllability, by adjusting the current or voltage of the control pole, you can precisely control the on-off and cutoff of the main circuit, so as to achieve accurate control of large current.

In addition, the thyristor also has the advantages of high voltage resistance, small forward voltage drop, no mechanical noise and wear. It is widely used in a variety of electronic equipment and electronic products, such as household appliances, industrial control, power electronics and other fields, as a controlled rectifier, inverter, frequency conversion, voltage regulation, contactless switch and other key components.

应用场景

APPLICATION



单向可控硅：是一种大功率电器元件，也称为晶闸管。其特点为具有可控的单向导电，在自动控制系统中，可作为大功率驱动器件，实现用小功率控件控制大功率设备。

Unidirectional Thyristor: It is a high-power electrical component, also known as a thyristor. It is characterized by controllable unidirectional conduction, and can be used as a high-power driving device in automatic control system to realize the control of high-power equipment with small power controls.

UNIDIRECTIONAL THYRISTOR

(P/N)	TYPE	VDRM (V)	IT (A)	VTM (V)	IH Max.(mA)	IGT Max.(mA)	VGT Max.(V)	PACKAGE
2KM7601	Silicon Controlled Rectifiers	600	0.8	1.5	5	0.2	0.8	SOT-23-3
2KM7602	Silicon Controlled Rectifiers	600	0.8	1.5	5	0.2	0.8	SOT-89
2KM7603	Silicon Controlled Rectifiers	600	1	1.5	5	0.2	0.8	SOT-223
2KM7604	Silicon Controlled Rectifiers	600	2	1.5	5	0.1	0.8	TO-252
2KM7607	Silicon Controlled Rectifiers	400/600	0.8	1.7	5	0.08	0.8	SOT-23
2KM7610	Silicon Controlled Rectifiers	400/600	2	1.55	3	0.2	0.8	TO-252
2KM7612	Silicon Controlled Rectifiers	600/800	4	1.8	5	0.2	0.8	TO-252
2KM7614	Silicon Controlled Rectifiers	600/800	6	1.8	5	0.2	0.8	TO-252
2KM7616	Silicon Controlled Rectifiers	600	8	1.75	25	15	1.5	TO-252
2KM7618	Silicon Controlled Rectifiers	800	12	1.5	60	15	1	TO-252
2KM7620	Silicon Controlled Rectifiers	800	16	1.5	30	20	1.5	TO-252
2KM7623	Silicon Controlled Rectifiers	800	25	1.4	60	40	1.5	TO-220

双向可控硅：是在普通可控硅的基础上发展而成的，不仅能代替两只反极性并联的可控硅，而且仅需一个触发电路，是比较理想的交流开关器件。

Bidirectional Thyristor: is developed on the basis of ordinary thyristor, not only can replace two reverse polarity parallel thyristor, and only one trigger circuit, is an ideal AC switching device.

BIDIRECTIONAL THYRISTOR

(P/N)	TYPE	VDRM (V)	IT (A)	VTM (V)	IH Max.(mA)	IGT Max.(mA)	VGT Max.(V)	PACKAGE
2KM7605	Triac	600/800	4	1.7	30	70	1.3	TO-252
2KM7606	Triac	600/800	1	1.5	5	7	1.5	SOT-223
2KM7608	Triac	400/600	0.8	1.8	10	5	1.5	SOT-23
2KM7609	Triac	600/800	1	1.5	5	5	1.5	SOT-223
2KM7611	Triac	600/800	4	1.7	20	20	1.3	SOT-223
2KM7613	Triac	600/800	6	1.7	30	10	1.5	TO-252
2KM7615	Triac	600/800	6	1.7	30	10	1.5	TO-252
2KM7617	Triac	600/800	8	1.65	60	10	1.5	TO-252
2KM7619	Triac	800	12	1.65	60	50	1.5	TO-252
2KM7621	Triac	800	16	1.55	50	20	1.3	TO-252
2KM7622	Triac	600/800	16	1.55	50	50	1.3	TO-220
2KM7624	Triac	600/800	20	1.7	50	50	1.5	TO-220
2KM7625	Triac	600/800	25	1.55	80	50	1.5	TO-220

SOT SERIES PACKAGE



SOT-23



SOT-23-3



SOT-89



SOT-223

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TO SERIES PACKAGE



TO220



TO252

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▶ 三极管，也称双极型晶体管、晶体三极管，是一种控制电流的半导体器件。其作用是把微弱信号放大成幅度值较大的电信号，也用作无触点开关。

三极管是半导体基本元器件之一，具有电流放大作用，是电子电路的核心元件。三极管是在一块半导体基片上制作两个相距很近的PN结，两个PN结把整块半导体分成三部分，中间部分是基区，两侧部分是发射区和集电区，排列方式有PNP和NPN两种。

Triode, also known as bipolar transistor, crystal triode, is a semiconductor device that controls current. Its role is to amplify the weak signal into a larger amplitude value of the electrical signal, but also used as a contactless switch.

Triode is one of the basic components of semiconductor, has the effect of current amplification, is the core component of electronic circuit. The transistor is in a semiconductor substrate to produce two PN junctions very close to each other, the two PN junctions divide the whole semiconductor into three parts, the middle part is the base region, the two sides of the part is the emission region and the collector region, the arrangement of PNP and NPN two kinds.

▶ 三极管应用

1. 放大作用

三极管最主要的功能就是放大功能。通过控制输入信号的大小，三极管可以对电流进行放大，从而实现对信号的增强。

2. 开关控制

三极管可以通过控制输入信号的高低电平，实现对电路的开关控制。开关作用基于三极管在电路中导通或截止的特性。

3. 稳压功能

三极管还具有稳压功能，可以用于稳定电压。通过调整三极管的工作状态，可以使电路的输出电压保持稳定。

Triode Application

1. Amplification

The main function of the transistor is the amplification function. By controlling the value of the input signal, the triode can amplify the current, thus achieving the enhancement of the signal.

2. Switch control

The triode can control the high and low level of the input signal to realize the switching control of the circuit. The switching action is based on the on-off or off-off characteristics of the triode in the circuit.

3. Voltage regulator function

The triode also has a voltage regulator function and can be used to stabilize the voltage. By adjusting the working state of the triode, the output voltage of the circuit can be kept stable.

应用场景

APPLICATION



PNP三极管：是由2块P型半导体中间夹着1块N型半导体所组成的三极管，所以称为PNP型三极管。

PNP Triode: It is a triode composed of 2 P-type semiconductors sandwiched by 1 N-type semiconductor, so it is called PNP triode.

PNP TRANSISTOR

(P/N)	POLAR (CH)	VCBO (V)	VCEO (V)	VEBO (V)	IC (V)	VCE(SAT) Typ.(V)	HFE	PD(W) (TC=25°C)	fr (MHz)	PACKAGE
2KA2001	PNP	40	40	6	0.2	0.3	100-300	0.2	250	SOT-23
2KA2002	PNP	60	60	5	0.4	0.25	100-300	0.25	200	SOT-23
2KA2003	PNP	160	150	5	0.6	0.5	100-300	0.3	100	SOT-23
2KA2004	PNP	60	50	5	0.1	0.3	200-400	0.2	180	SOT-23
2KA2005	PNP	40	25	5	0.5	0.6	200-350	0.3	150	SOT-23
2KA2006	PNP	40	25	6	0.8	0.5	200-350	0.3	150	SOT-23
2KA2007	PNP	40	40	5	0.6	0.75	100-300	0.3	200	SOT-23
2KA7030DV	PNP	160	150	5	0.2	0.5	100-300	0.3	100	SOT-23-6
2KA7031DV	PNP	55	35	5	2	0.3	200-400	0.625	100	SOT-23-6
2KB4001	PNP	40	25	5	1.5	0.5	200-350	0.3	100	SOT-23
2KB4003	PNP	50	45	5	0.5	0.7	250-630	0.3	100	SOT-23
2KB4004	PNP	40	32	5	1	0.5	180-390	0.5	150	SOT-89
2KB4005	PNP	40	30	6	3	0.5	160-320	0.5	50	SOT-89
2KB4006	PNP	40	32	5	2	0.8	180-390	0.5	100	SOT-89
2KB4007	PNP	120	120	5	0.7	0.6	200-400	0.25	75	SOT-89
2KB4008	PNP	50	50	5	2	0.5	120-240	2	120	SOT-89
2KB4009	PNP	180	140	6	4	0.37	100-300	0.25	110	SOT-89
2KB4010	PNP	55	35	5	2	0.3	200-400	3	100	SOT-23
2KB4015	PNP	180	140	6	4	0.37	100-300	0.3	110	SOT-233
2KB4016	PNP	32	20	5	1	0.5	100-250	3	40	SOT-223
2KB4017	PNP	100	80	5	1	0.5	100-250	1.35	115	SOT-223
2KB4018	PNP	100	100	6	0.8	0.5	100-300	0.3	120	SOT-23

NPN三极管：是指由两块N型半导体中间夹着一块P型半导体所组成的三极管；也称为晶体三极管，可以说它是电子电路中最重要器件。三极管是电子电路中最重要器件，它最主要的功能是电流放大和开关作用，它可以把微弱的电信号变成一定强度的信号，当然这种转换仍然遵循能量守恒，它只是把电源的能量转换成信号的能量。

NPN Triode: refers to a triode composed of two N-type semiconductors sandwiched between a P-type semiconductor; Also known as the transistor, it can be said that it is the most important device in electronic circuits. The transistor is the most important device in the electronic circuit, its main function is the current amplification and switching, it can turn the weak electrical signal into a certain strength signal, of course, this conversion still follows the conservation of energy, it is only the energy of the power supply transfer to the energy of the signal.

NPN TRANSISTOR

(P/N)	POLAR (CH)	VCBO (V)	VCEO (V)	VEBO (V)	IC (V)	VCE(SAT) Typ.(V)	HFE	PD(W) (TC=25°C)	fr (MHz)	PACKAGE
2KC1001	NPN	60	40	6	0.2	0.3	100-300	0.2	300	SOT-23
2KC1001A	NPN	60	40	6	0.2	0.3	100-300	0.2	300	SOT-23
2KC1002	NPN	70	40	6	0.6	0.3	100-300	0.25	300	SOT-23
2KC1003	NPN	180	160	6	0.6	0.5	100-300	0.3	100	SOT-23
2KC1004	NPN	60	50	5	0.1	0.3	200-400	0.2	250	SOT-23
2KC1005	NPN	40	25	5	0.5	0.6	200-350	0.3	150	SOT-23
2KC1006	NPN	40	25	6	0.8	0.5	200-350	0.3	150	SOT-23
2KC1007	NPN	30	30	5	0.1	0.6	200-450	0.25	100	SOT-23
2KC1008	NPN	60	40	6	0.6	0.75	100-300	0.3	250	SOT-23
2KC1009	NPN	400	400	6	0.2	0.3	80-300	0.35	50	SOT-23
2KC1010	NPN	300	300	5	0.5	0.2	100-300	0.35	50	SOT-23
2KD3001	NPN	50	50	6	1.2	0.5	160-320	0.25	100	SOT-23
2KD3003	NPN	50	45	5	0.5	0.7	250-630	0.3	100	SOT-23
2KD3004	NPN	40	32	5	1	0.4	180-390	0.5	150	SOT-89
2KD3005	NPN	40	30	6	3	0.5	160-320	0.5	50	SOT-89
2KD3006	NPN	120	120	5	0.7	0.6	200-400	2	90	SOT-89
2KD3007	NPN	60	50	6	2	0.4	200-400	0.5	150	SOT-89
2KD3009	NPN	100	80	5	1	0.5	100-250	1.3	115	SOT-223
2KD3010	NPN	140	100	6	0.8	0.5	100-300	0.3	120	SOT-23

高频三极管：高频三极管一般应用在 VHF, UHF, CATV, 无线遥控、射频模块等高频宽带低噪声放大器上，这些使用场合大都用在低电压、小信号、小电流、低噪声条件下，其功率最大 2.25瓦，集电极电流最大 500 毫安。

High-Frequency triode: high-frequency triode is generally used in VHF, UHF, CATV, wireless remote control, RF modules and other high-frequency broadband low noise amplifiers, these applications are mostly used in low voltage, small signal, small current, low noise conditions, its power maximum 2.25 watts, collector current maximum 500 mA.

HIGH FREQUENCY TRANSISTOR

(P/N)	POLAR (CH)	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	VCE(SAT) Ttp.(V)	HFE	PD(W) (TC=25°C)	ft (MHz)	PACKAGE
2KC1101	NPN	20	12	3	0.1	0.4	125-250	0.2	7000	SOT-23
2KC1102	NPN	20	12	3	0.1	0.4	125-250	0.2	7000	SOT-23-3
2KC1103	NPN	20	11	3	0.05	0.7	100-200	0.15	3500	SOT-23
2KC1104	NPN	20	11	3	0.05	0.7	100-200	0.15	3500	SOT-23-3
2KC1105	NPN	30	15	5	0.05	0.5	70-190	0.2	600	SOT-23
2KD3008	NPN	20	12	3	0.1	0.4	125-250	1.2	6500	SOT-89

数字三极管：带电阻的晶体管，有的仅在基极上串联一只电阻R1，有的在基极与发射极之间还并联一只电阻R2。

Digital Triode: transistor with resistance, some only series a resistor R1 on the base, and some also parallel a resistor R2 between the base and the emitter.

DIGITAL TRANSISTOR

(P/N)	POLAR (CH)	VCBO (V)	VCEO (V)	IC (A)	R1 (KΩ)	R2 (KΩ)	VO(on) Max.(V)	GI (Min.)	PD(W) (TC=25°C)	ft (MHz)	PACKAGE
KTC100	NPN	50	40	0.1	10	10	0.3	30	0.2	250	SOT-23
KTC101	NPN	50	50	0.1	4.7	10	0.3	100	0.2	250	SOT-23
KTC102	NPN	50	50	0.1	4.7	47	0.3	80	0.2	250	SOT-23
KTC103	NPN	50	50	0.1	47	47	0.3	68	0.2	250	SOT-23
KTC104	NPN	50	12	0.1	2.2	10	0.3	33	0.2	250	SOT-23
KTA200	PNP	50	50	0.1	4.7	—	0.3	100	0.2	250	SOT-23
KTA201	PNP	50	30	0.1	4.7	4.7	0.3	30	0.2	250	SOT-23

复合三极管：是将两个和更多个晶体管的集电极连在一起，而将第一只晶体管的发射极直接耦合到第二只晶体管的基极，依次连接而成，最后引出E、B、C三个电极。

Composite Triode: The collector of two and more transistors is connected together, and the emitter of the first transistor is directly coupled to the base of the second transistor, connected in turn, and finally leads to E, B, and C three electrodes.

COMPOUND TRANSISTOR

(P/N)	POLAR (CH)	VCBO (V)	VCEO (V)	VEBO (V)	IC (A)	VCE(SAT) Typ.(V)	HFE	PD(W) (TC=25°C)	ft (MHz)	PACKAGE
2KA7030DV	Dual PNP	-160	-150	-5	-0.2	-0.5	100-300	0.3	300	SOT-23-6
2KC6001DV	Dual NPN	180	160	6	-0.2	-0.2	100-300	0.3	300	SOT-23-6

SOT SERIES PACKAGE



SOT-23



SOT-23-3



SOT-23-6



SOT-223



SOT-89

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▶ 二极管是一种具有不对称电导的两个端子（阴阳两极接线端，故名“二极管”）的电子元件，此二极管使其原则上仅允许电流作单方向传导，它在一个方向为低电阻，高电流，而在另一个方向为高电阻。

二极管经常用在把交流电压和电流转换成直流电压和电流的电路中（如AC/DC电源）。

二极管也常用于电压的倍增电路，电压平移电路，限压电路和稳压电路中。

A diode is an electronic component with asymmetric conductance of two terminals (anode and cathode terminals, so the name "two"), which allows it in principle to only allow current to conduct in one direction, it is low resistance in one direction, high current, and high resistance in the other direction.

Diodes are often used in circuits that convert AC voltage and current into DC voltage and current (such as AC/DC power supplies).

Diodes are also commonly used in voltage multiplication circuits, voltage translation circuits, voltage limiting circuits and voltage regulator circuits.

▶ 二极管应用

半导体二极管的非线性电流-电压特性，可以根据选择不同的半导体材料和掺杂不同的杂质从而形成杂质半导体来改变。特性改变后的二极管在使用上除了用做开关的方式之外，还有很多其他的功能，如：用来调节电压（齐纳二极管），限制高电压从而保护电路（雪崩二极管），无线电调谐（变容二极管），产生射频振荡已经产生光等。

Diode Application

The nonlinear current-voltage characteristics of semiconductor diodes can be changed according to the selection of different semiconductor materials and doping of different impurities to form impurity semiconductors. The changed characteristics of the diode in use in addition to the way used as a switch, there are many other functions, such as: to regulate the voltage (Zener diode), limit high voltage to protect the circuit (avalanche diode), radio tuning (varcasting diode), generate RF oscillation has generated light and so on.

应用场景

APPLICATION



肖特基势垒二极管：是一种导通电压降低、允许高速切换的二极管，是利用肖特基势垒特性而产生的电子元件。

Schottky Barrier diode: A diode with a low on-voltage drop that allows high-speed switching, is an electronic component that takes advantage of Schottky barrier properties.

SCHOTTKY BARRIER DIODE

(P/N)	Config	VR (V)	IF (A)	ID (A)	VF @IF (V)	IR @VR (μA)	Cj (pF)	R ^θ JA (°C/W)	PACKAGE
1KK2102A	Single	20	1	30	0.55	300	110	90	SMA
1KK2104A	Single	40	1	30	0.55	300	110	90	SMA
1KK2106A	Single	60	1	30	0.7	300	80	90	SMA
1KK2110A	Single	100	1	30	0.85	200	80	90	SMA
1KK2115A	Single	150	1	30	0.9	100	80	90	SMA
1KK2120A	Single	200	2	50	0.9	100	80	90	SMA
1KK2202A	Single	20	2	50	0.55	500	220	80	SMA
1KK2204A	Single	40	2	50	0.55	500	220	80	SMA
1KK2206A	Single	60	2	50	0.7	500	80	80	SMA
1KK2210A	Single	100	2	50	0.85	300	80	80	SMA
1KK2215A	Single	150	2	50	0.95	300	80	80	SMA
1KK2220A	Single	200	2	50	0.95	300	80	80	SMA
1KK2302A	Single	20	3	80	0.55	500	450	70	SMA
1KK2304A	Single	40	3	80	0.55	500	450	70	SMA
1KK2306A	Single	60	3	80	0.7	500	400	70	SMA
1KK2310A	Single	100	3	80	0.85	300	400	70	SMA
1KK2315A	Single	150	3	80	0.95	300	400	70	SMA
1KK2320A	Single	200	3	80	0.95	300	400	70	SMA
1KK2504A	Single	40	5	150	0.55	1000	500	60	SMA
1KK2204B	Single	40	2	50	0.55	500	220	75	SMB
1KK2206B	Single	60	2	50	0.7	500	80	75	SMB
1KK2210B	Single	100	2	50	0.85	300	80	75	SMB
1KK2215B	Single	150	2	50	0.95	300	80	75	SMB
1KK2220B	Single	200	2	50	0.95	300	80	75	SMB
1KK2302B	Single	20	3	80	0.55	500	450	65	SMB
1KK2304B	Single	40	3	80	0.55	500	450	65	SMB
1KK2306B	Single	60	3	80	0.7	500	400	65	SMB
1KK2310B	Single	100	3	80	0.85	300	400	65	SMB
1KK2315B	Single	150	3	80	0.95	300	400	65	SMB
1KK2320B	Single	200	3	80	0.95	300	400	65	SMB
1KK2504B	Single	40	5	150	0.55	1000	500	55	SMB
1KK2506B	Single	60	5	150	0.7	1000	300	55	SMB
1KK2510B	Single	100	5	150	0.85	1000	300	55	SMB
1KK2515B	Single	150	5	150	0.85	1000	300	55	SMB
1KK2520B	Single	200	5	150	0.85	1000	300	55	SMB
1KK2102E	Single	20	1	25	0.45	1000	110	100	SOD-123
1KK2104E	Single	40	1	25	0.6	1000	110	100	SOD-123
1KK2102D	Single	20	1	30	0.55	300	110	100	SOD-123FL
1KK2104D	Single	40	1	30	0.55	300	110	100	SOD-123FL
1KK2202D	Single	20	2	50	0.55	500	220	85	SOD-123FL
1KK2204D	Single	40	2	50	0.55	500	220	85	SOD-123FL
1KK2206D	Single	60	2	50	0.7	500	80	85	SOD-123FL
1KK2210D	Single	100	2	50	0.85	300	80	85	SOD-123FL
1KK2215D	Single	150	2	50	0.95	300	80	85	SOD-123FL
1KK2220D	Single	200	2	50	0.95	300	80	85	SOD-123FL
1KK2302D	Single	20	3	80	0.55	500	250	80	SOD-123FL
1KK2304D	Single	40	3	80	0.55	500	250	80	SOD-123FL
1KK2306D	Single	60	3	80	0.75	300	160	80	SOD-123FL
1KK2310D	Single	100	3	80	0.85	300	160	80	SOD-123FL
1KK2315D	Single	150	3	80	0.95	300	160	80	SOD-123FL
1KK2320D	Single	200	3	80	0.95	300	160	80	SOD-123FL
1KK2102F	Single	20	1	25	0.45	1000	110	200	SOD-323
1KK2104F	Single	40	1	25	0.6	1000	110	200	SOD-323
1KK2701	Single	30	0.2	0.6	0.8	2	10	430	SOT-23

SCHOTTKY BARRIER DIODE

(P/N)	Config	VR (V)	IF (A)	ID (A)	VF @IF (V)	IR @VR (μA)	Cj (pF)	R ^θ JA (°C/W)	PACKAGE
1KK2003G	Single	30	0.2	1	0.5	30	10	500	SOD-523
1KK2004E	Single	40	0.35	1.5	0.6	5	50	300	SOD-123
1KK2004F	Single	40	0.35	1.5	0.6	5	10	500	SOD-323
1KK2204AF	Single	40	2	50	0.55	150	220	80	SMAF
1KK2301F	Single	10	3	5	0.38	15	30	100	SOD-323
1KK2702	Dual,CA	30	0.2	0.6	0.8	2	10	430	SOT-23
1KK2703	Dual,CC	30	0.2	0.6	0.8	2	10	430	SOT-23
1KK2704	Dual,Series	30	0.2	0.6	0.8	2	10	430	SOT-23

快恢复二极管：是一种具有开关特性好、反向恢复时间短特点的二极管，主要引用于开关电源、PWM脉宽调制器、变频器等电子电路中。

Fast Recovery diode: It is a diode with good switching characteristics and short reverse recovery time. It is mainly used in electronic circuits such as switching power supply, PWM pulse width modulator and frequency converter.

FAST RECOVERY DIODE

(P/N)	VR (V)	IF (A)	IFSM (A)	VF @IF (V)	IR @VR (μA)	trr (ns)	Cj (pF)	R ^θ JA (°C/W)	PACKAGE
1KF1120A	200	1	30	1.0	5	35	15	75	SMA
1KF1160A	600	1	30	1.7	5	35	15	75	SMA
1KF1170A	1000	1	30	1.7	5	35	15	75	SMA
1KF2120A	200	1	30	1.0	5	50	15	50	SMA
1KF2160A	600	1	30	1.7	5	75	15	50	SMA
1KF2170A	1000	1	30	1.7	5	75	15	50	SMA
1KF3120A	200	1	30	1.3	5	150	15	50	SMA
1KF3160A	600	1	30	1.3	5	250	15	50	SMA
1KF3170A	1000	1	30	1.3	5	500	15	50	SMA
1KF2102D	200	1	30	1.3	5	150	15	85	SOD-123FL
1KF2106D	600	1	30	1.3	5	250	15	85	SOD-123FL
1KF2107D	1000	1	30	1.3	5	500	15	85	SOD-123FL

整流二极管：一种将交流电能转变为直流电能的半导体器件。

Rectifier Diode: A semiconductor device that converts alternating current electrical energy into direct current electrical energy.

RECTIFIER DIODE

(P/N)	VR (V)	IF (A)	IFSM (A)	VF @IF (V)	IR @VR (μA)	Cj (pF)	R ^θ JA (°C/W)	PACKAGE
1KR3101A	50	1	30	1.1	5	15	75	SMA
1KR3104A	400	1	30	1.1	5	15	75	SMA
1KR3107A	1000	1	30	1.1	5	15	75	SMA
1KR3101D	50	1	30	1.1	5	8	90	SOD-123FI
1KR3104D	400	1	30	1.1	5	8	90	SOD-123FI
1KR3107D	1000	1	30	1.1	5	8	90	SOD-123FL

开关二极管：是为在电路上进行“开”、“关”而特殊设计制造的二极管，主要应用于电子计算机、脉冲和开关电路中。

Switching Diode: It is a diode specially designed and manufactured for "on" and "off" on the circuit, mainly used in electronic computers, pulse and switching circuits.

SWITCHING DIODE

(P/N)	Config	VR (V)	IF (A)	IFSM (A)	VF @IF (V)	IR @VR (μA)	trr (ns)	Cj (pF)	PACKAGE
1KS1010F	Single	100	0.15	0.3	1.25	1	4	2	SOD-323
1KS1011F	Single	200	0.2	0.625	1.25	0.1	50	1.5	SOD-323
1KS1012F	Single	130	0.25	2	1.25	1	4	2	SOD-323
1KS3001	Dual,CC	75	0.15	1	1.25	2.5	4	2	SOT-23
1KS3002	Dual,CA	75	0.215	1	1.25	1	4	1.5	SOT-23
1KS3003	Dual,Series	75	0.215	1	1.25	1	4	1.5	SOT-23
1KS3004	Single	75	0.215	1	1.25	1	4	1.5	SOT-23
1KS3005	Dual,CC	250	0.2	0.625	1.25	0.1	50	5	SOT-23
1KS3006	Dual,CA	250	0.2	0.625	1.25	0.1	50	5	SOT-23
1KS3007	Dual,CC	250	0.2	0.625	1.25	0.1	50	5	SOT-23
1KS3008	Dual,Series	250	0.2	0.625	1.25	0.1	50	5	SOT-23
1KS3009	Dual,Series	120	0.2	0.3	1.25	0.1	50	1.5	SOT-23
1KS3010E	Single	100	0.15	0.3	1.25	1	4	2	SOD-123
1KS3011E	Single	250	0.2	0.625	1.25	0.1	50	5	SOD-123
1KS3012	Dual,Series	150	0.215	1	1.25	1	4	1.5	SOT-23
1KS3013	Dual,CC	100	0.215	1	1.25	1	4	1.5	SOT-23
1KS4001G	Single	80	0.1	0.225	1.2	0.1	4	3	SOD-523

齐纳（稳压）二极管：是利用二极管在反向作用下的齐纳击穿效应，制造而成的一种具有稳定电压功能的电子元件。

Zener (voltage regulator) diode: It is an electronic component with stable voltage function that is manufactured by using the Zener breakdown effect of the diode under reverse action.

ZENER DIODE

(P/N)	PD (mW)	Stable voltage range VZ @IZ=5mA			Dynamic impedance ZZT @ IZ=5mA Max(Ω)	Reverse leakage current IR @VR		Forward voltage VF @ IF=10mA (V)	PACKAGE
		Nom (V)	Min (V)	Max (V)		Max(μA)	VR (V)		
1KZ1F2V4C	200	2.4	2.28	2.52	85	100	1	0.9	SOD-323
1KZ1F2V7C	200	2.7	2.57	2.84	83	75	1	0.9	SOD-323
1KZ1F3V0C	200	3	2.85	3.15	95	50	1	0.9	SOD-323
1KZ1F3V3C	200	3.3	3.14	3.47	95	25	1	0.9	SOD-323
1KZ1F3V6C	200	3.6	3.42	3.78	95	15	1	0.9	SOD-323
1KZ1F3V9C	200	3.9	3.71	4.1	95	10	1	0.9	SOD-323
1KZ1F4V3C	200	4.3	4.09	4.52	95	5	1	0.9	SOD-323
1KZ1F4V7C	200	4.7	4.47	4.94	78	5	1	0.9	SOD-323
1KZ1F5V1C	200	5.1	4.85	5.36	60	0.1	1	0.9	SOD-323
1KZ1F5V6C	200	5.6	5.32	5.88	40	0.1	1	0.9	SOD-323
1KZ1F6V2C	200	6.2	5.89	6.51	10	0.1	2	0.9	SOD-323
1KZ1F6V8C	200	6.8	6.46	7.14	8	0.1	3	0.9	SOD-323
1KZ1F7V5C	200	7.5	7.13	7.88	7	0.1	5	0.9	SOD-323
1KZ1F8V2C	200	8.2	7.79	8.61	7	0.1	6	0.9	SOD-323
1KZ1F9V1C	200	9.1	8.65	9.56	10	0.1	7	0.9	SOD-323
1KZ1F10C	200	10	9.5	10.5	15	0.1	7.5	0.9	SOD-323
1KZ1F11C	200	11	10.45	11.55	20	0.1	8.5	0.9	SOD-323
1KZ1F12C	200	12	11.4	12.6	20	0.1	9	0.9	SOD-323
1KZ1F13C	200	13	12.35	13.65	25	0.1	10	0.9	SOD-323
1KZ1F15C	200	15	14.25	15.75	30	0.1	11	0.9	SOD-323
1KZ1F16C	200	16	15.2	16.8	40	0.1	12	0.9	SOD-323
1KZ1F18C	200	18	17.1	18.9	50	0.1	14	0.9	SOD-323
1KZ1F20C	200	20	19	21	50	0.1	15	0.9	SOD-323
1KZ1F22C	200	22	20.9	23.1	55	0.1	17	0.9	SOD-323
1KZ1F24C	200	24	22.8	25.2	80	0.1	18	0.9	SOD-323
1KZ1F27C	200	27	25.65	28.35	80	0.1	20	0.9	SOD-323

ZENER DIODE

(P/N)	PD (mW)	Stable voltage range VZ @IZ=5mA			Dynamic impedance ZZT @ IZ=5mA Max(Ω)	Reverse leakage current IR @VR		Forward voltage VF @ IF=10mA (V)	PACKAGE
		Nom (V)	Min (V)	Max (V)		Max(μA)	VR (V)		
1KZ1F30C	200	30	28.5	31.5	80	0.1	22.5	0.9	SOD-323
1KZ1F33C	200	33	31.35	34.65	80	0.1	25	0.9	SOD-323
1KZ1F36C	200	36	34.2	37.8	90	0.1	27	0.9	SOD-323
1KZ1F39C	200	39	37.05	40.95	90	0.1	29	0.9	SOD-323
1KZ1F43C	200	43	40.85	45.15	100	100	32	0.9	SOD-323
1KZ1F47C	200	47	44.65	49.35	100	75	35	0.9	SOD-323
1KZ2E2V2C	500	2.2	2.08	2.33	100	50	0.7	0.9	SOD-123
1KZ2E2V7C	500	2.7	2.5	2.9	110	25	1	0.9	SOD-123
1KZ2E3VOC	500	3	2.8	3.2	120	15	1	0.9	SOD-123
1KZ2E3V3C	500	3.3	3.1	3.5	130	10	1	0.9	SOD-123
1KZ2E3V6C	500	3.6	3.4	3.8	130	5	1	0.9	SOD-123
1KZ2E3V9C	500	3.9	3.7	4.1	130	5	1	0.9	SOD-123
1KZ2E4V3C	500	4.3	4	4.6	130	0.1	1	0.9	SOD-123
1KZ2E4V7C	500	4.7	4.4	5	130	0.1	1	0.9	SOD-123
1KZ2E5V1C	500	5.1	4.8	5.4	130	2	1.5	0.9	SOD-123
1KZ2E5V6C	500	5.6	5.2	6	80	1	2.5	0.9	SOD-123
1KZ2E6V2C	500	6.2	5.8	6.6	50	1	3	0.9	SOD-123
1KZ2E6V8C	500	6.8	6.4	7.2	30	0.5	3.5	0.9	SOD-123
1KZ2E7V5C	500	7.5	7	7.9	30	0.5	4	0.9	SOD-123
1KZ2E8V2C	500	8.2	7.7	8.7	30	0.5	5	0.9	SOD-123
1KZ2E9V1C	500	9.1	8.5	9.6	30	0.5	6	0.9	SOD-123
1KZ2E10C	500	10	9.4	10.6	30	0.1	7	0.9	SOD-123
1KZ2E12C	500	12	11.4	12.7	35	0.1	9	0.9	SOD-123
1KZ2E15C	500	15	13.8	15.6	40	0.1	11	0.9	SOD-123
1KZ2E18C	500	18	16.8	19.1	45	0.1	13	0.9	SOD-123
1KZ2E20C	500	20	18.8	21.2	50	0.1	15	0.9	SOD-123
1KZ2E22C	500	22	20.8	23.3	55	0.1	17	0.9	SOD-123
1KZ2E24C	500	24	22.8	25.6	60	0.1	19	0.9	SOD-123
1KZ2E27C	500	27	25.1	28.9	70	0.1	21	0.9	SOD-123
1KZ2E30C	500	30	28	32	80	0.1	23	0.9	SOD-123
1KZ2E33C	500	33	31	35	80	0.1	25	0.9	SOD-123
1KZ2E36C	500	36	34	38	90	0.1	27	0.9	SOD-123
1KZ2E39C	500	39	37	41	100	2	30	0.9	SOD-123
1KZ2E43C	500	43	40	46	130	2	33	0.9	SOD-123
1KZ2E47C	500	47	44	50	150	2	36	0.9	SOD-123

ESD保护二极管：是一种过压、防静电保护元件，是为高速数据传输应用的I/O端口保护设计的器件，用来避免电子设备中的敏感电路受到ESD（静电放电）的影响。

ESD Protection diode: is an overvoltage, anti-static protection element, is designed for high-speed data transmission applications I/O port protection devices, to avoid the sensitive circuit in electronic equipment by ESD (electrostatic discharge).

ESD PROTECTION DIODE

(P/N)	IEC 61000-4-2		VRWM (V)	IR @ VRWM (μA)	VBR @ IT=1mA (V)	IPP (A)	PPK (W)	VC@IPP (W)	Cj (pF)	PACKAGE
	Air (kV)	Contact (kV)								
1KE05-4	±15	±8	5	5	6	25	500	20	6	SOT-143
1KE05-6	±15	±8	5	5	6	12	300	17.5	3	SOT-23-6
1KE1G3V0	±15	±8	3	2.5	4.0	11.0	100	9.8	80	SOD-523
1KE1G3VOC	±15	±8	3	2.5	4.0	11.0	100	9.8	80	SOD-523
1KE1G3V3	±15	±8	3.3	2.5	5.0	9.8	102	10.4	80	SOD-523
1KE1G3V3C	±15	±8	3.3	2.5	5.0	9.8	102	10.4	65	SOD-523
1KE1G5V0	±15	±8	5.0	1.0	6.2	8.7	107	12.3	65	SOD-523
1KE1G5V0C	±15	±8	5.0	1.0	6.2	8.7	107	12.3	65	SOD-523
1KE1I3V0	±15	±8	3.0	2.5	4.0	11.0	100	9.8	80	SOD-882
1KE1I3V0C	±15	±8	3.0	2.5	4.0	11.0	100	9.8	80	SOD-882
1KE1I3V3	±15	±8	3.3	2.5	5.0	9.8	102	10.4	80	SOD-882

ESD PROTECTION DIODE

(P/N)	IEC 61000-4-2		VRWM (V)	IR @ VRWM (μ A)	VBR @ IT=1mA (V)	IPP (A)	PPK (W)	VC@IPP (W)	Cj (pF)	PACKAGE
	Air (kV)	Contact (kV)								
1KE1I3V3C	± 15	± 8	3.3	2.5	5.0	9.8	102	10.4	80	SOD-882
1KE1I5V0	± 15	± 8	5.0	1.0	6.2	8.7	107	12.3	65	SOD-882
1KE1I5V0C	± 15	± 8	5.0	1.0	6.2	8.7	107	12.3	65	SOD-882
1KE3F3V3	± 15	± 8	3.3	5.0	4.0	12	350	19.0	3	SOD-323
1KE3F3V3C	± 15	± 8	3.3	5.0	4.0	12	350	19.0	3	SOD-323
1KE3F5V0	± 15	± 8	5.0	5.0	6.0	12	350	18.3	3	SOD-323
1KE3F5V0C	± 15	± 8	5.0	5.0	6.0	12	350	18.3	3	SOD-323
1KE3F8V0	± 15	± 8	8.0	2.0	8.5	12	350	18.5	3	SOD-323
1KE3F8V0C	± 15	± 8	8.0	2.0	8.5	12	350	18.5	3	SOD-323
1KE3F12V	± 15	± 8	12	1.0	13.3	12	350	28.6	3	SOD-323
1KE3F12VC	± 15	± 8	12	1.0	13.3	12	350	28.6	3	SOD-323
1KE3I3V0C	± 15	± 8	3	2.5	4	11.0	100	10.4	80	SOD-882
1KE3I3V3C	± 15	± 8	3.3	2.5	5	9.8	102	20	80	SOD-882
1KE3I5V0	± 15	± 8	5	1.0	6.2	8.7	107	12.3	65	SOD-882
1KE3I5V0C	± 15	± 8	5	1.0	6.2	8.7	107	12.3	65	SOD-882
1KE61089DY	± 15	± 8	170	5	112	40	6.5	112	100	SOP-8

请注意：带有额外“C”后缀的部件号是双向设备。
 Note: Part numbers with an additional "C" suffix are bidirectional components.

SOT SERIES PACKAGE



SOT-23



SOT-23-6



SOT-143



SOT-523

...

SOD SERIES PACKAGE



SOD-123



SOD-123FL



SOD-323



SOD-882

...

SM SERIES PACKAGE



SMAF



SMA



SMB

...

SOP SERIES PACKAGE



SOP-8

...

► 集成电路 (Integrated Circuit) 是一种微型电子器件或部件。采用一定的工艺，把一个电路中所需的晶体管、电阻、电容和电感等元件及布线互连一起，制作在一小块或几小块半导体晶片或介质基片上，然后封装在一个管壳内，成为具有所需电路功能的微型结构；其中所有元件在结构上已组成一个整体，使电子元件向着小型化、低功耗、智能化和高可靠性方面迈进了一大步。

An Integrated Circuit is a tiny electronic device or component. Using a certain process, the transistors, resistors, capacitors and inductors required in a circuit and wiring are interconnected together, made on a small or several small pieces of semiconductor chips or dielectric substrates, and then packaged in a tube shell to become a miniature structure with the required circuit functions; All components have been structurally formed as a whole, making electronic components a big step forward in terms of miniaturization, low power consumption, intelligence and high reliability.

► 集成电路应用

集成电路有着多种优势，分别能够简化系统结构、提高性能和可靠性、降低功耗、实现数字化和智能化以及节省成本和资源。

集成电路同时在计算机、通信、工控、医疗、汽车等领域应用非常广泛。

Integrated Circuit Application

Integrated circuits have many advantages, which can simplify system structure, improve performance and reliability, reduce power consumption, realize digitalization and intelligence, and save costs and resources.

Integrated circuits are widely used in computer, communication, industrial control, medical treatment, automobile and other fields.

应用场景

APPLICATION



三端稳压集成电路：是一种直到临界反向击穿电压前都具有很高电阻的半导体器件，广泛应用于稳压电源与限幅电路中。

Three-Terminal regulated integrated circuit: A semiconductor device with high resistance up to the critical reverse breakdown voltage, widely used in regulated power supplies and limiter circuits.

THREE TERMINAL VOLTAGE REGULATOR

(P/N)	VIN Max.(V)	VOUT (V)	IO (A)	PD (W) (TC=25°C)	Iq Max.(mA)	PACKAGE
KA180005	30	5	0.1	0.5	6	SOT-89
KA180006	30	6	0.1	0.5	6	SOT-89
KA180008	30	8	0.1	0.5	6	SOT-89
KA180010	30	10	0.1	0.5	6	SOT-89
KA180012	30	12	0.1	0.5	6	SOT-89
KA180015	30	15	0.1	0.5	6	SOT-89
KA280M05	35	5	0.5	1.25	6	TO-252
KA280M06	35	6	0.5	1.25	6	TO-252
KA280M08	35	8	0.5	1.25	6	TO-252
KA280M10	35	10	0.5	1.25	6	TO-252
KA280M12	35	12	0.5	1.25	6	TO-252
KA280M15	35	15	0.5	1.25	6	TO-252
KA190005	30	-5	0.1	0.5	6	SOT-89
KA190006	30	-6	0.1	0.5	6	SOT-89
KA190008	30	-8	0.1	0.5	6	SOT-89
KA190010	30	-10	0.1	0.5	6	SOT-89
KA080Q05	30	5	0.1	0.35	6	SOT-23
KA080Q06	30	6	0.1	0.35	6	SOT-23
KA080Q08	30	8	0.1	0.35	6	SOT-23
KA090Q05	30	-5	0.1	0.35	6	SOT-23
KA100130	26	3	0.1	0.25	0.02	SOT-89
KA100133	26	3.3	0.1	0.25	0.02	SOT-89
KA100136	26	3.6	0.1	0.25	0.02	SOT-89
KA100144	26	4.4	0.1	0.25	0.02	SOT-89
KA100150	26	5	0.1	0.25	0.02	SOT-89
KA100M317	40	Adj	1.5	1.25	12	SOT-223
KA200M317	40	Adj	1.5	1.25	12	TO-252

电源管理集成电路：是一种特定用途的集成电路，其功能是为系统作管理电源等工作。

Power management integrated circuit: is a specific purpose integrated circuit, its function is to manage the power supply of the main system.

LITHIUM ION/POLYMER BATTERY PROTECTION IC

(P/N)	Overcharge detection voltage [VOCP](V)	Overcharge release voltage [VOCR](V)	Overdischarge detection voltage [VODP](V)	Overcurrent detection voltage [VOI1](mV)	Overdischarge release voltage [VODR](V)	PACKAGE
KP00Q01	4.3±0.05	4.1±0.05	2.4±0.1	150±30	3.0±0.1	SOT-23-6
KP00Q02	4.3±0.05	4.1±0.05	2.4±0.1	150±30	3.0±0.1	SOT-23-6
KP00Q03	4.3±0.05	4.1±0.05	2.4±0.1	150±30	3.0±0.1	SOT-23-5
KP00Q04	4.3±0.05	4.1±0.05	2.4±0.1	150±30	3.0±0.1	ESOP-8
KP00Q05	4.28±0.05	4.08±0.05	2.4±0.1	150±30	3.0±0.1	SOT-23-6

DC DC CONVERTER CONTROL CIRCUITS

(P/N)	Power Supply Voltage [VCC](V)	Threshold Voltage [Vth](V)	Frequency [fOSC](Khz)	Current Limit Sense Voltage [Vipk](mV)	Switch Current [ISW](A)	PACKAGE
KM34063	40	1.25	100	300	1.5	SOP-8
KM34064	40	1.25	100	300	1.2	SOP-8
KM34065	40	1.25	100	300	0.8	SOP-8

ADJUSTABLE ACCURATE REFERENCE SOURCE

(P/N)	Cathode Voltage [VKA](V)	Cathode Current [IKA](mA)	Dynamic Impedance [ZKA](Ω)	Reference Input Voltage [VREF](V)	Power Dissipation [PD](mW)	PACKAGE
KA000Q431	36	150	0.15	2.5	350	SOT-23
KA000Q432	15	100	0.2	1.24	350	SOT-23

LITHIUM BATTERY MANAGEMENT

(P/N)	Regulator output voltage [VFLOAT](V)	Input supply voltage [VIN](V)	BAT pin current [IBAT](mA)	PROG pin voltage [VPROG](V)	Power dissipation [PD](mW)	PACKAGE
KX4054A	4.2±0.042	4.25-6.5	500	1.1	250	SOT-23-5
KX4057	4.2±0.042	4.0-7.0	500	1.0	250	SOT-23-6

运算放大集成电路：是具有很高放大倍数的电路单元，在实际电路中，通常结合反馈网络共同组成某种功能模块，是一种带有特殊耦合电路及反馈的放大器。

Operational Amplifier integrated circuit: it is a circuit unit with a high magnification. In the actual circuit, it is usually combined with a feedback network to form a certain functional module. It is an amplifier with a special coupling circuit and feedback.

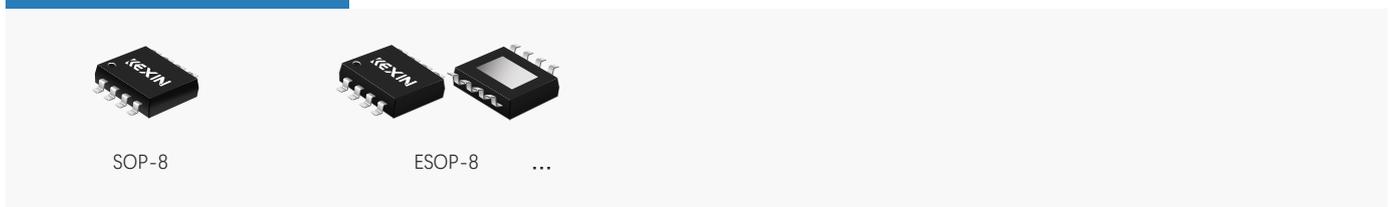
OPERATION AMPLIFIER

(P/N)	Power Supply Voltage [VCC](V)	Input Offset Voltage [VIO](mV)	Power Supply Current [ICC](mA)	Common-Mode Rejection [CMMR](dB)	Output Short Circuit [ISC](mA)	PACKAGE
KM358	32	7	3	65	60	SOP-8
KM393	36	5	2.5	60	60	SOP-8
KM4558	30	6	5.7	70	60	SOP-8
KM5532	22	5	16	70	60	SOP-8

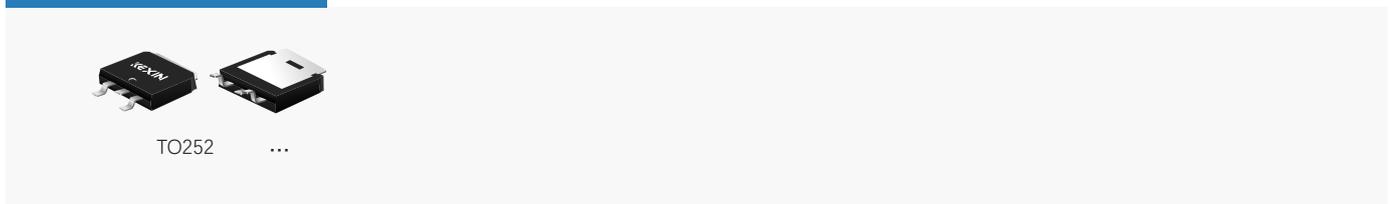
SOT SERIES PACKAGE



SOP SERIES PACKAGE



TO SERIES PACKAGE



PACKAGING SIZE

PACKAGING SPECIFICATIONS			
REEL PACKAGING			
PACKAGE	REEL SIZE(7inches)	REEL SIZE(13inches)	TAPE WIDTH(mm)
TO-263		800	24
TO-252		2500	16
SOT-223	1000	2500	12
SOT-89	1000	2500	12
SOT-89-5	1000	2500	12
SOT-23	3000	10000	8
SOT-23-6	3000	10000	8
SOT-23-5	3000	10000	8
SOT-23-3	3000	10000	8
SOT-363	3000	10000	8
SOT-323	3000	10000	8
SOT-523	3000		8
SOT-723	8000		9
SMC		3000	16
SMB		3000	12
SMA	2000	5000	12
SOD-123	3000	10000	8
SOD-123F	3000	10000	8
SOD-123FL	3000	10000	8
SOD-323	3000	10000	8
SOD-523	3000		8
SOD-723	8000		8
SOD-882	10000		8
TSSOP-8		2500	16
SOP-8		2500	12
DFN2x2	3000		8
PDFN3.3x3.3		5000	12
PDFN5x6		5000	12

封装常用不同标识及最小包装数量
 Different labels and minimum packaging quantities are commonly used for packaging



我们专注，因为我们专心

Add: 深圳市龙岗区坪地街道山塘尾工业区富心路三巷6号

Add: NO.6, 3 Lane, Fuxin Road, Shantangwei, Pingdi Street, Longgang Distric, Shenzhen, China

E-mail: kexin@kexin.com.cn

Http://www.kexin.com.cn

Tel: +86-755-83896222

Fax: +86-755-83897333

Hotline: 400-8833-228



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